



Docket No.: 50090-233

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Yukihiro NAGAI, et al.

Serial No.: 09/631,623

Filed: August 04, 2000

For: SEMICONDUCTOR DEVICE HAVING A POTENTIAL FUSE, AND METHOD
OF MANUFACTURING THE SAME

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office
Action dated December 19, 2001.

IN THE SPECIFICATION:

Please amend the paragraph bridging page 2 and 3 as follows:

In another aspect, the semiconductor device comprises a plurality of surface insulating films formed on a surface of the active region of the semiconductor substrate, and the surface insulating films are formed [in a] at different thicknesses [thickness each other]. A plurality of conductive films are formed on each of the surface insulating films.

Then, one of the surface insulating films having smaller thickness is caused to break down and to work as an electric fuse.